

## Silicon NPN Power Transistors

2SC940

## DESCRIPTION

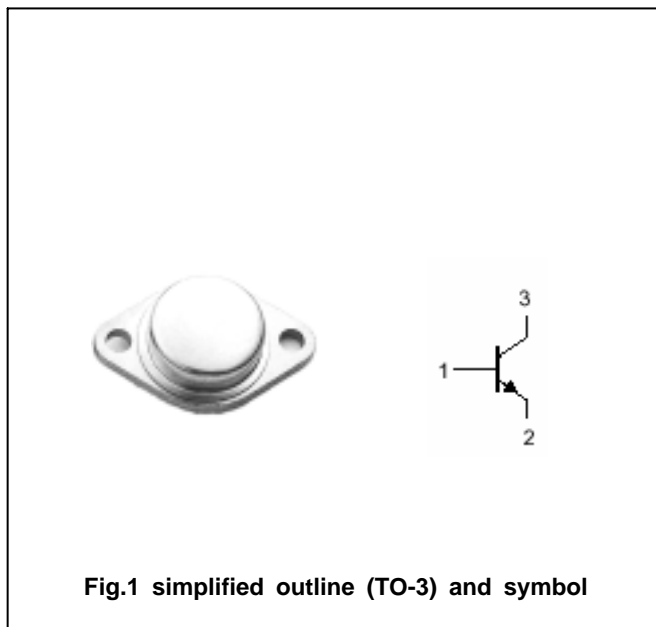
- With TO-3 package
- High current capability
- Wide area of safe operation

## APPLICATIONS

- For B/W TV horizontal deflection application

## PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	200	V
$V_{CEO}$	Collector-emitter voltage	Open base	90	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current		7.5	A
$I_{CM}$	Collector current-peak		15	A
$P_T$	Total power dissipation	$T_{mb}=25$	50	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-65~150	

## Silicon NPN Power Transistors

## 2SC940

## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA ; I <sub>B</sub> =0	90			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA ; I <sub>C</sub> =0	7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =5A ; I <sub>B</sub> =0.5A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =90V ; I <sub>E</sub> =0			0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V ; I <sub>C</sub> =0			0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =5A ; V <sub>CE</sub> =5V	15		70	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =10V		20		MHz

◆ h<sub>FE-2</sub> Classifications

O	Q	P
15-35	25-45	35-70

Silicon NPN Power Transistors

2SC940

PACKAGE OUTLINE

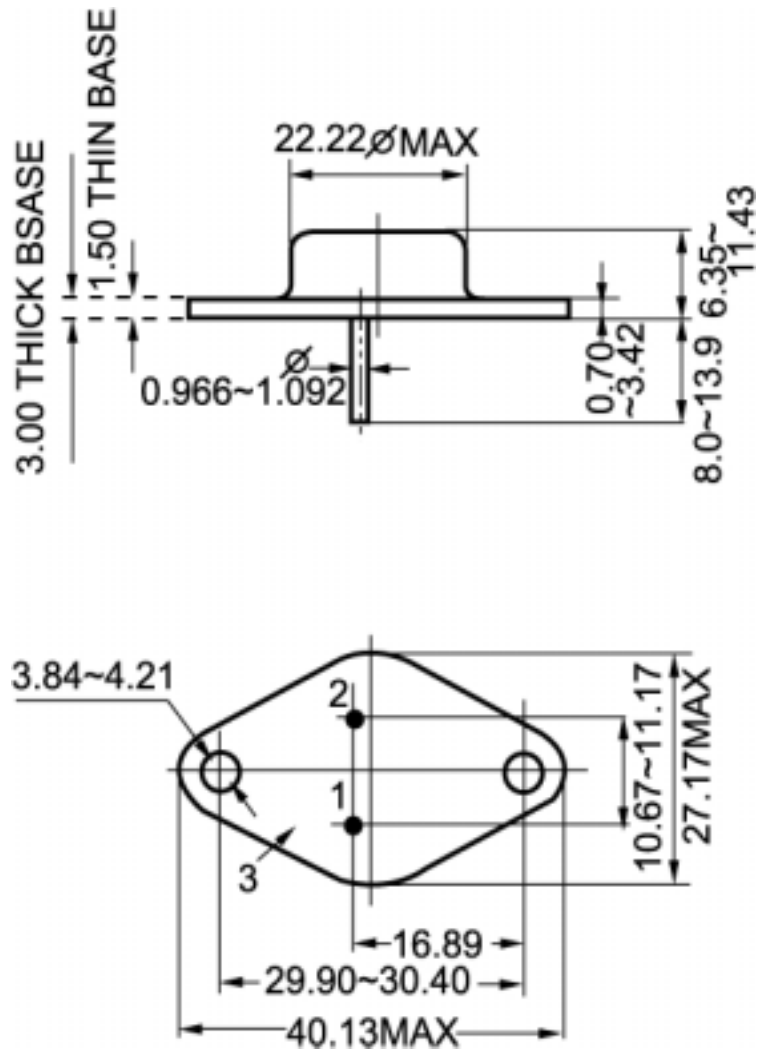


Fig.2 Outline dimensions